

CPIX14

(Workshop on Active CMOS Pixel Sensors for Particle Tracking)

# X-ray Image Sensors for SACLA and Future Ultimate Storage Ring Light Sources

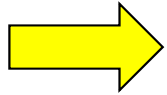
September 17, 2014

RIKEN\*, University of Hyogo\*\*  
Nobukazu Teranishi\*,\*\* and Takaki Hatsui\*

# Collaborators

- RIKEN, JASRI
  - All members of SACLA members, especially,*
  - Togo Kudo, Takashi Kameshima, Shun Ono, Kyosuke Ozaki, Kazuo Kobayashi, Yoichi Kirihara, Masahiko Omodani
- Univ. of Hyogo
  - Takeo Watanabe, Hiroo Kinoshita
- SOIPIX collaboration
  - esp.* **Yasuo Arai** (KEK), Ikuo Kurachi (KEK), Jiro Ida (Kanazawa Inst. of Technology), Takeshi Tsuru (Kyoto Univ.) , Kazuhiko Hara (Unv. of Tsukuba)
- Private Sector
  - e2v Technologies, Meisei Electric, Lapis Semiconductor, A-R-Tec Corp.
- Detector Advisory Committee
  - **Peter Denes** (Chair, LBNL), Andrew Holland (The Open Univ.), Grzegorz Deputch (Fermilab), **Yasuo Arai** (KEK)

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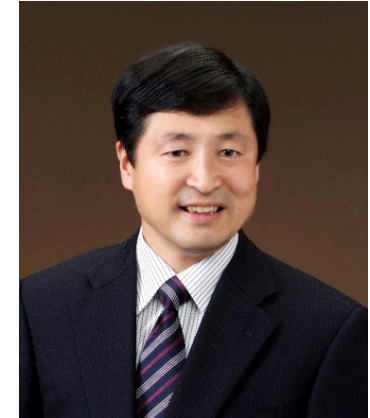


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3. MPCCD (Multi-Port CCD)
4. SOPHIAS (Silicon-On-Insulator Photon Imaging Array Sensor)
5. New Image Sensor Plan
6. Summary

# Self-introduction

## Nobukazu Teranishi

- 1978–2000, **NEC**
- 2000–2013, **Panasonic**
- 2013–present, **U. of Hyogo, Shizuoka U., RIKEN**



I have developed **image sensors** and **cameras** for 35 years since 1978.

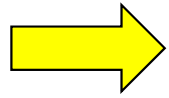
- Invented “**pinned photodiode**”
- Wafer process (**Dark current**, microlens, color filter, **small pixel**, ...)
- Design (**CCD, CMOS**, noise, ...)
- Camera (First **USB camera**, mosaic color filter arrangement, ...)

## Developing

- **X-ray** image sensors
- **Visible photon counting** image sensors
- Image sensors with **new functions**

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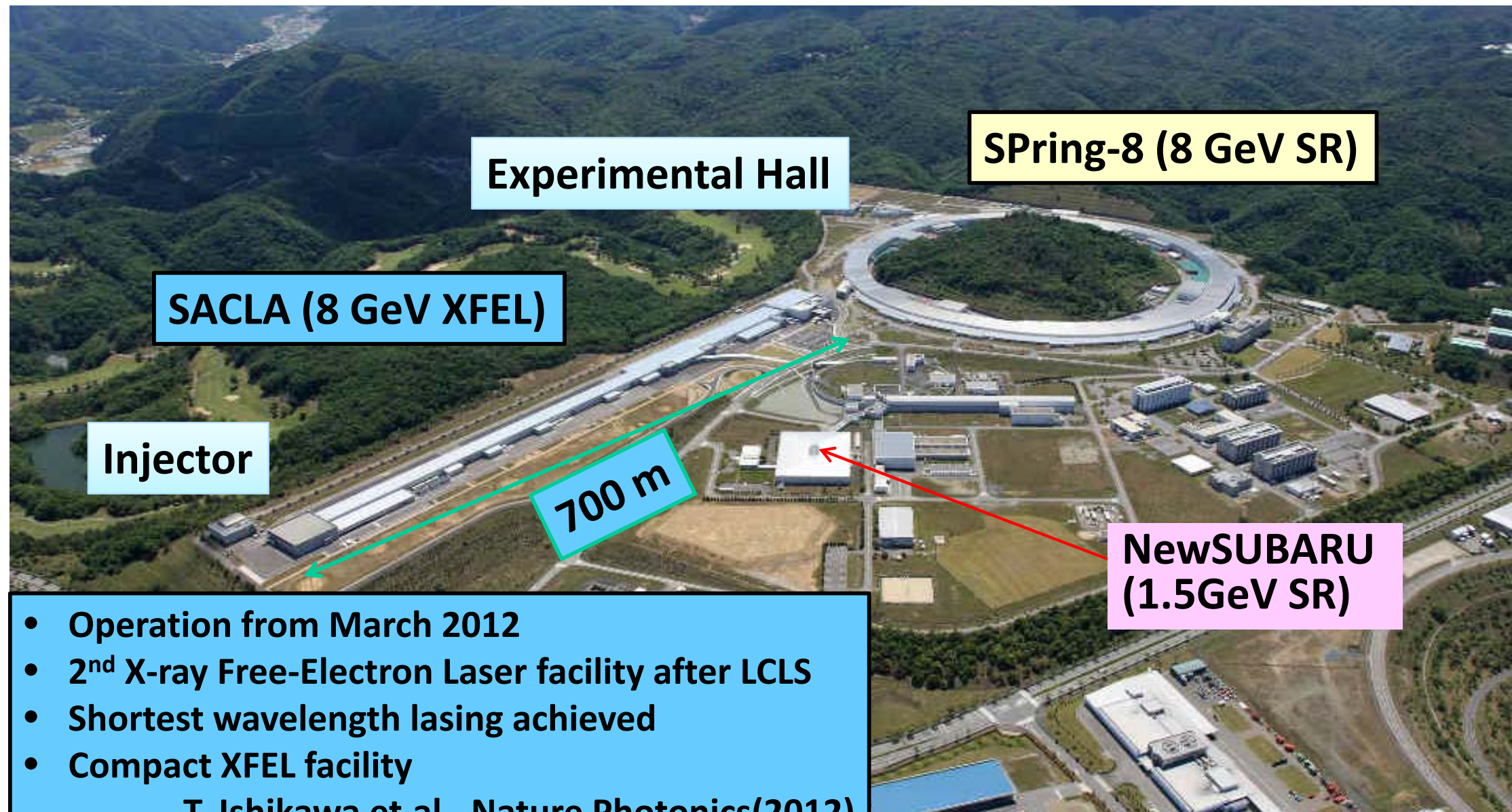
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# SPring-8 Campus

## SPring-8, SACLA, and NewSUBARU

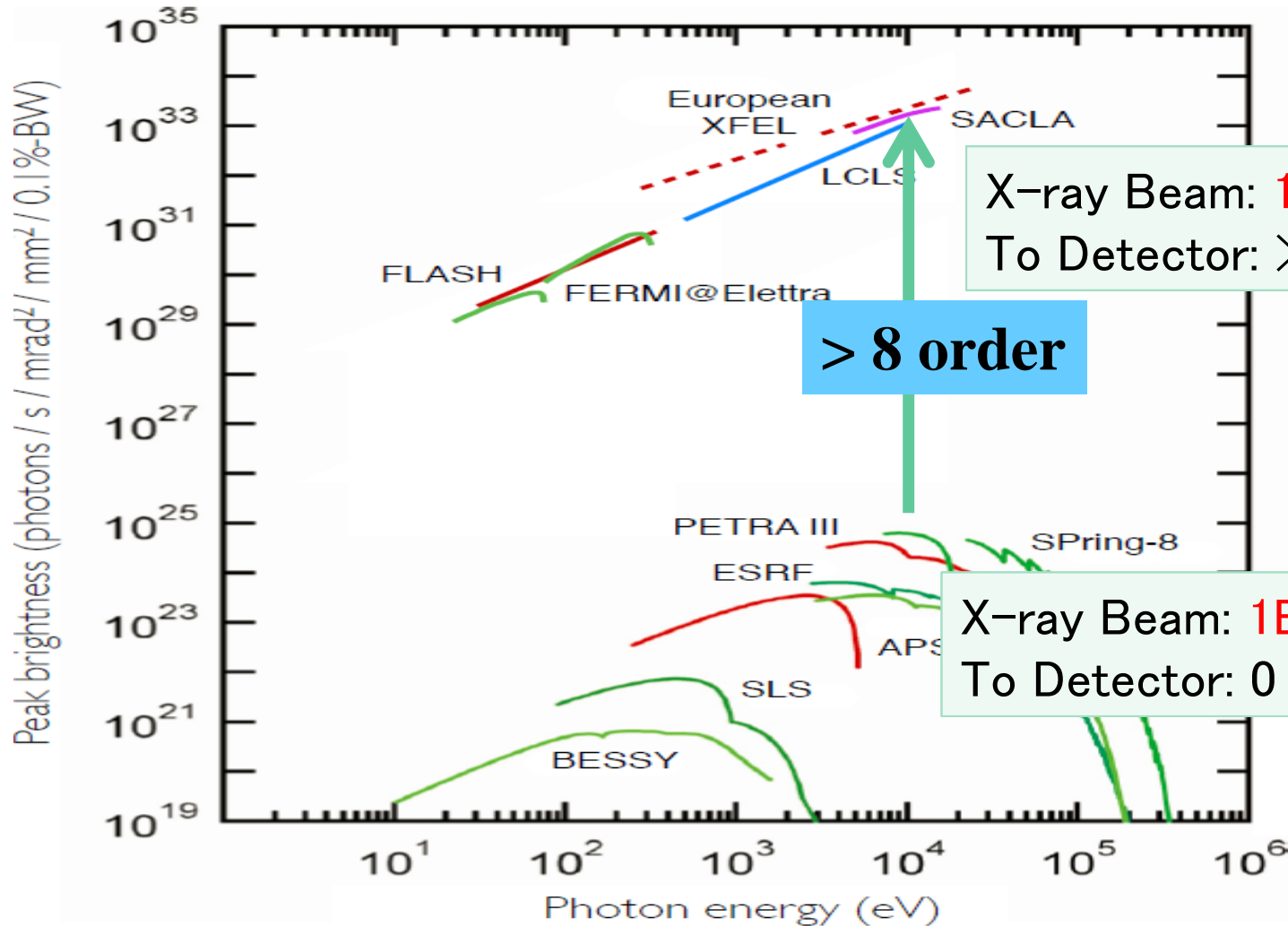


- Operation from March 2012
- 2<sup>nd</sup> X-ray Free-Electron Laser facility after LCLS
- Shortest wavelength lasing achieved
- Compact XFEL facility

T. Ishikawa et.al., Nature Photonics(2012)

# X-ray Free-Electron Lasers

- Integration mode X-ray image sensors are needed.

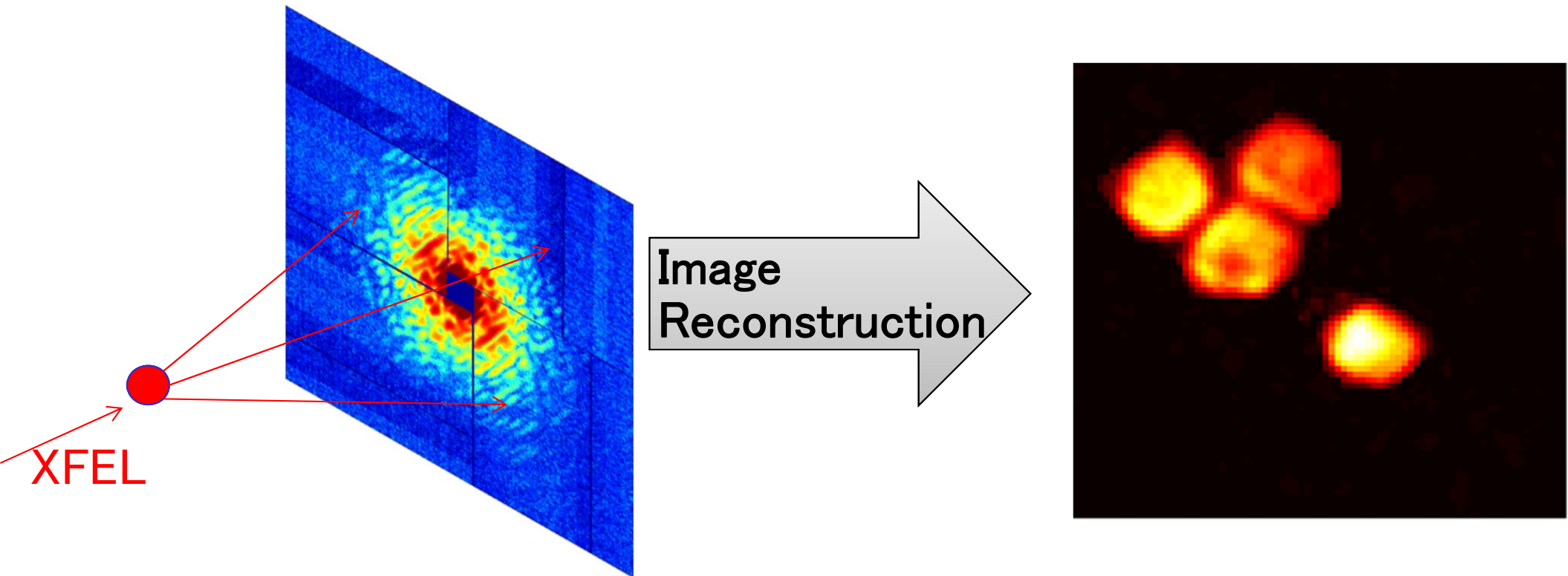


Peter Schmüser, Martin Dohlus, Jörg Rossbach, Christopher Behrens  
 “Free-Electron Lasers in the Ultraviolet and X-Ray Regime Physical Principles, Experimental Results, Technical Realization” Springer Tracts in Modern Physics, Vol. 258 (2014) 2<sup>nd</sup> Eds.

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# Scientific Experiments at SACLA

Target: Nano scale dynamics of materials  
by coherent X-ray diffraction Imaging



## Diffraction Pattern

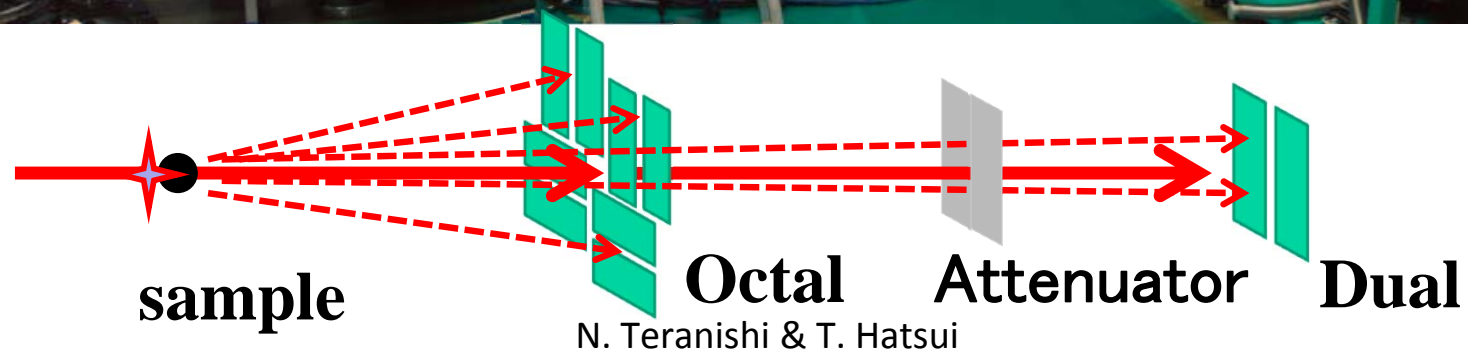
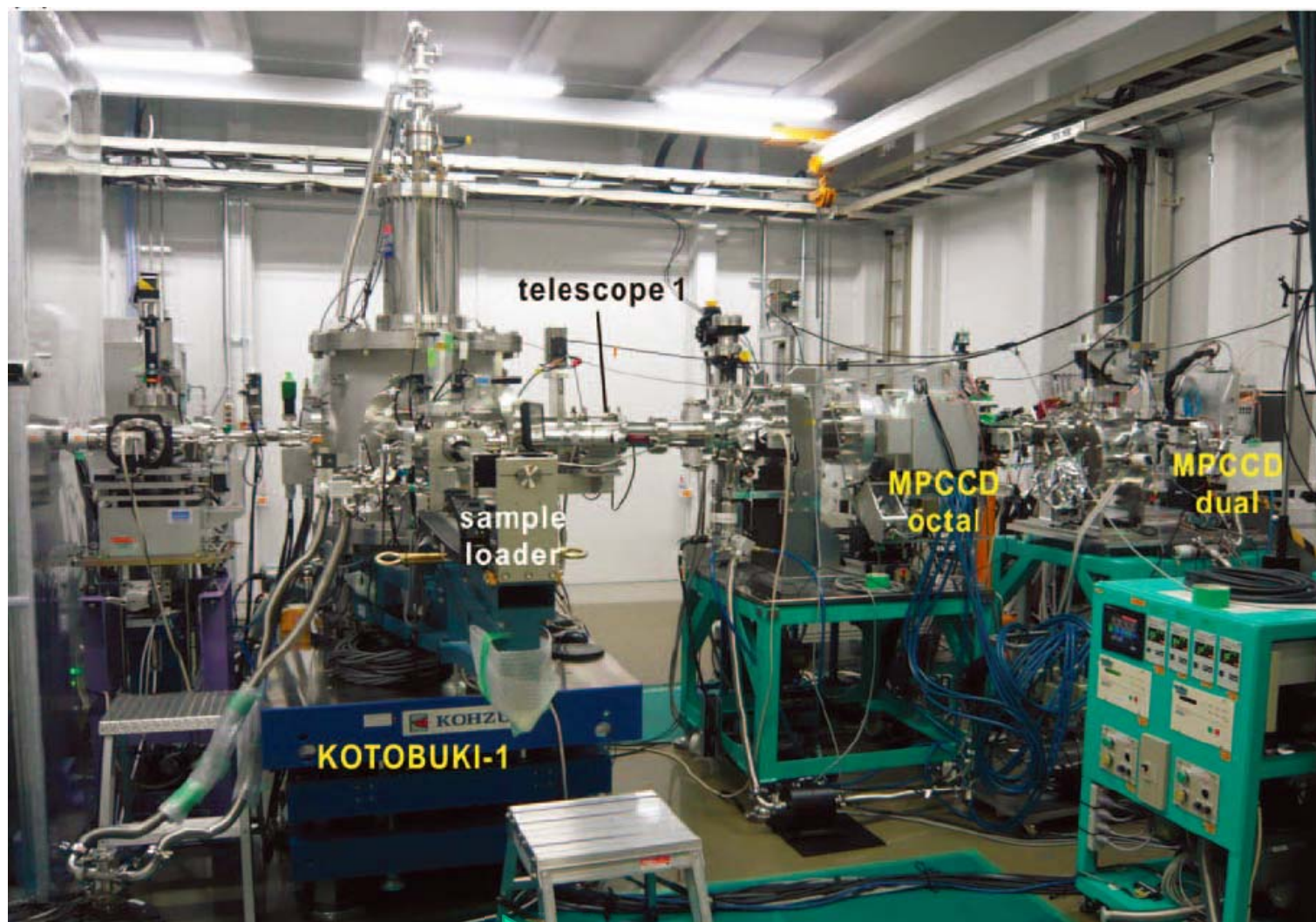
- MPCCD  
(Custom Multi-port CCD)

## Real Space Image

- Gold nano particles  
Diameter of about 100 nm
- Spatial resolution: 8 nm  
(C. Song et.al.)

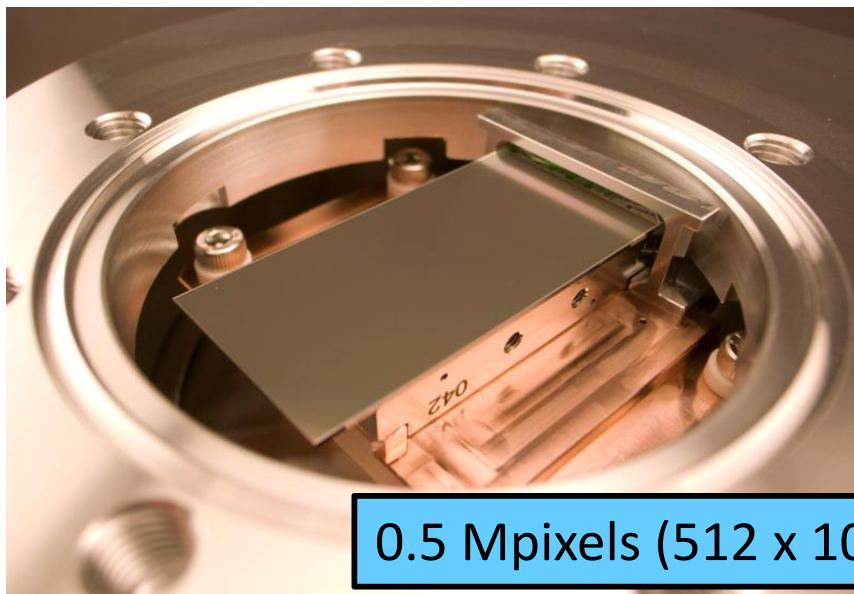


# Setup with Octal and Dual MPCCD

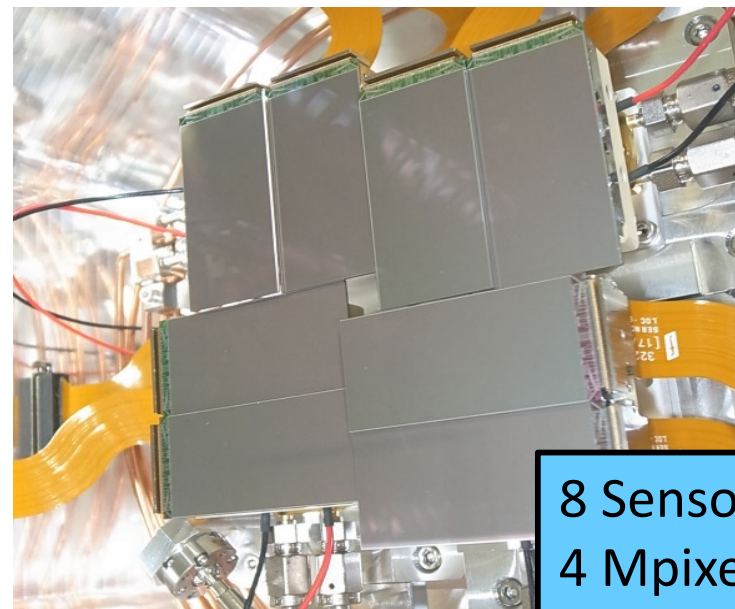


# Detector Family

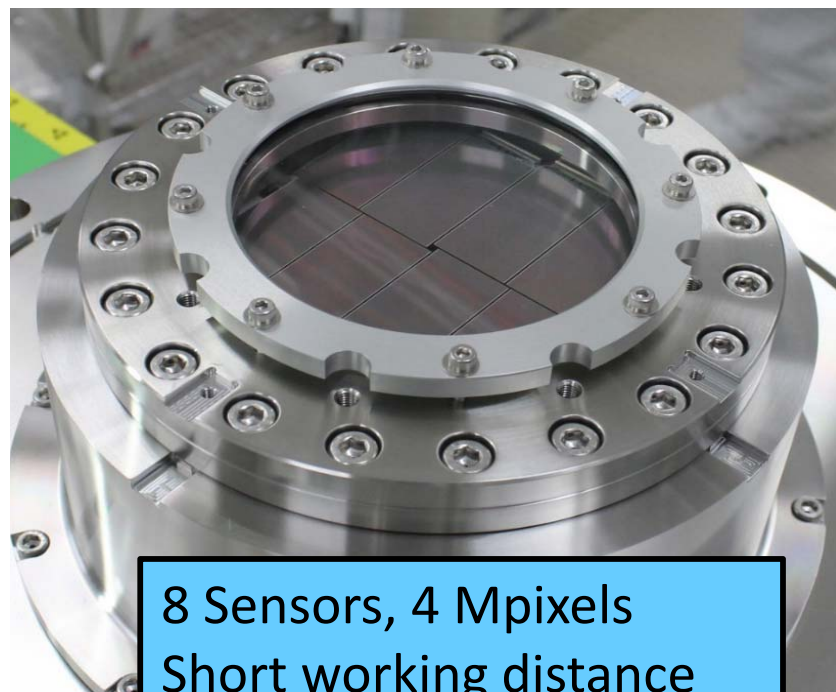
Kameshima et.al., Rev. Sci. Instrum. 85, 033110 (2014).



0.5 Mpixels (512 x 1024 )



8 Sensors  
4 Mpixels



8 Sensors, 4 Mpixels  
Short working distance

- Current Deployment
  - 8 detectors (Totally 31 sensors)
  - 70–80% applications are covered.**
- March 2015
  - 14 detectors (45 sensors)
- Increases at  $\sim 20$  sensors/year

# Imaging Live Cell in Micro-Liquid Enclosure by X-ray Laser Diffraction

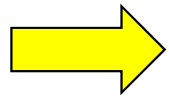
(T. Kimura et.al., Nature Communications 5, Article number: 3052)

Photos are not available.

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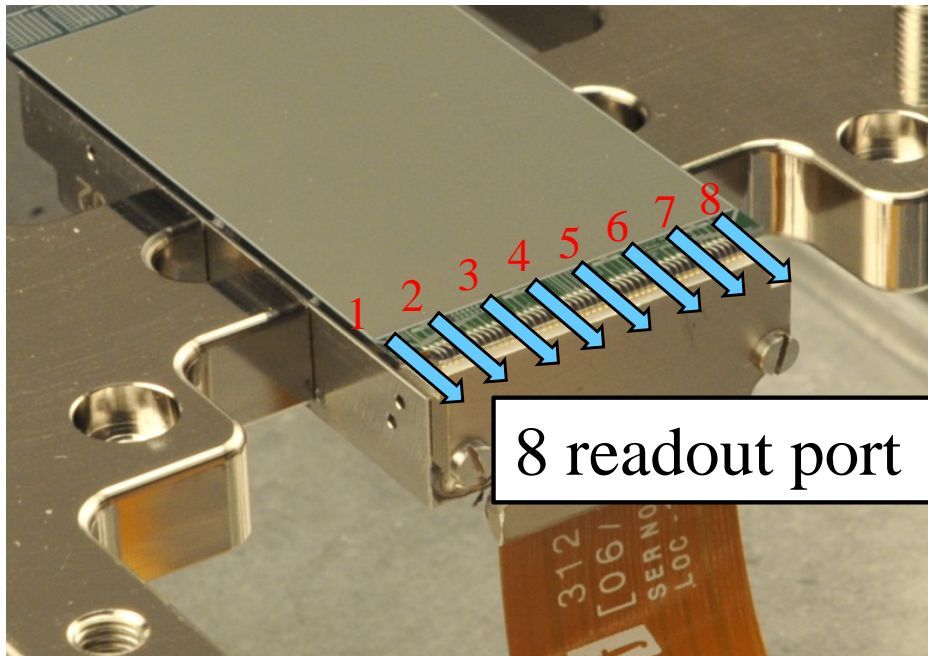
5. New Image Sensor Plan

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# MPCCD Phase I (Multi-Port CCD)

## Requirements

- Radiation hardness
- Large dynamic range
  - ✓ Single photon detection
  - ✓ Large peak signal



## MPCCD Phase I specification

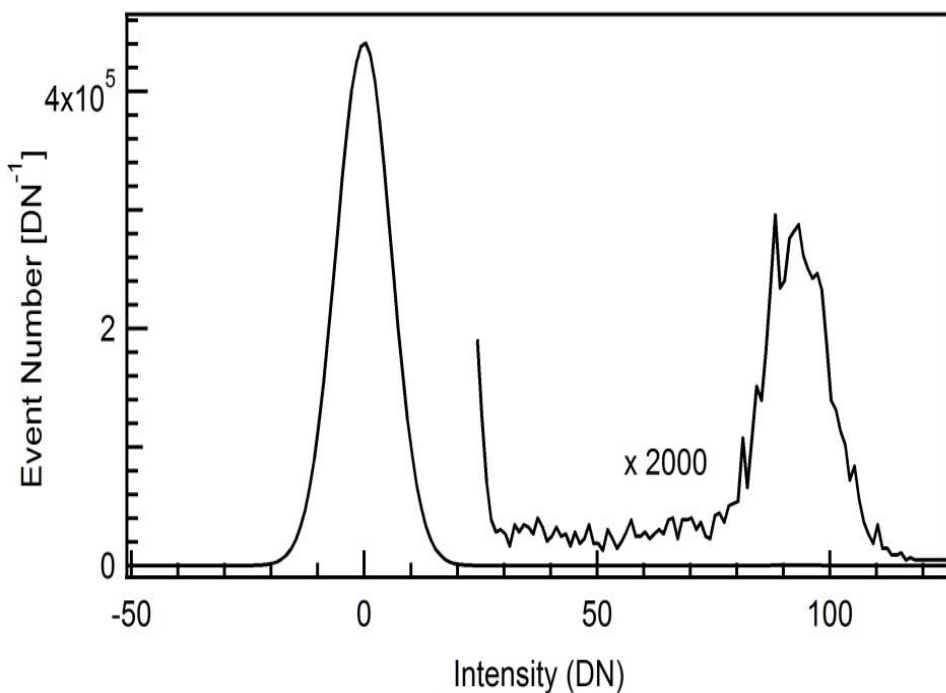
- Pixel size: 50  $\mu\text{m}$   $\square$
- # of pixels: 512 (H) x 1024 (V)
- Frame rate: 60 fps
- Peak signal: 4.1–5  $\text{Me}^-$   
2.5–3.0 kphoton@6 keV
- Detector noise: 100–250  $\text{e}^-$  rms  
0.06–0.15 photon@6 keV
- Sensor thickness: 50 $\mu\text{m}$
- PSF: 3  $\mu\text{m}$  @ 2  $\text{Me}^-$  Injection
- Radiation hardness:  
116 Mrad  
( $3.2 \times 10^{14}$  photon/ $\text{mm}^2$ @12 keV)

(T. Kameshima et.al., Review of Scientific Instruments, 85, 033110 (2014).

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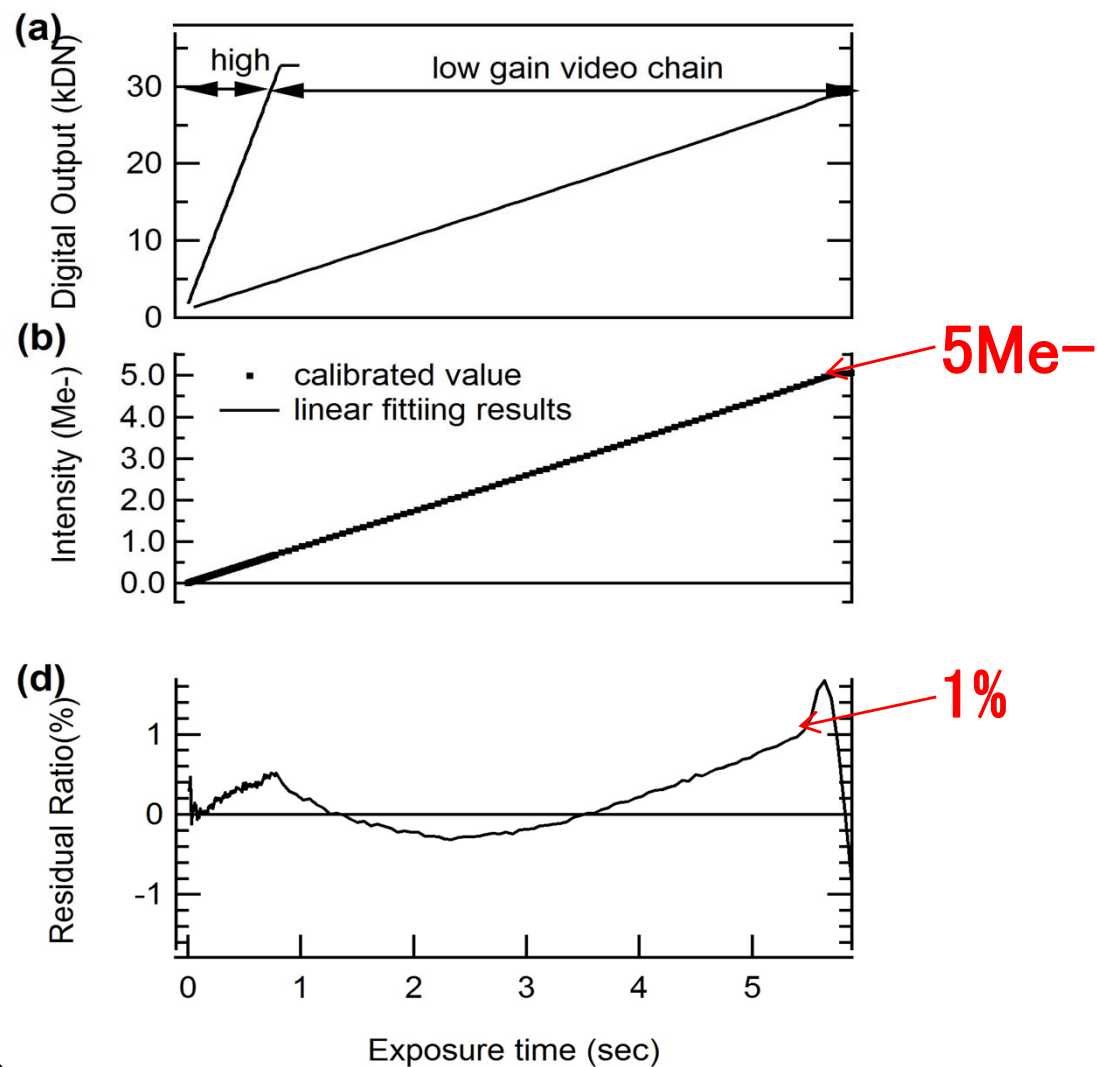
# MPCCD Phase I Performance: Noise and Peak Signal

Single photon Detection  
Fe55 (5.9 keV)



Peak signal and linearity

(Camera has 2 gain chains.)



# MPCCD Phase III and Phase III-L under Development

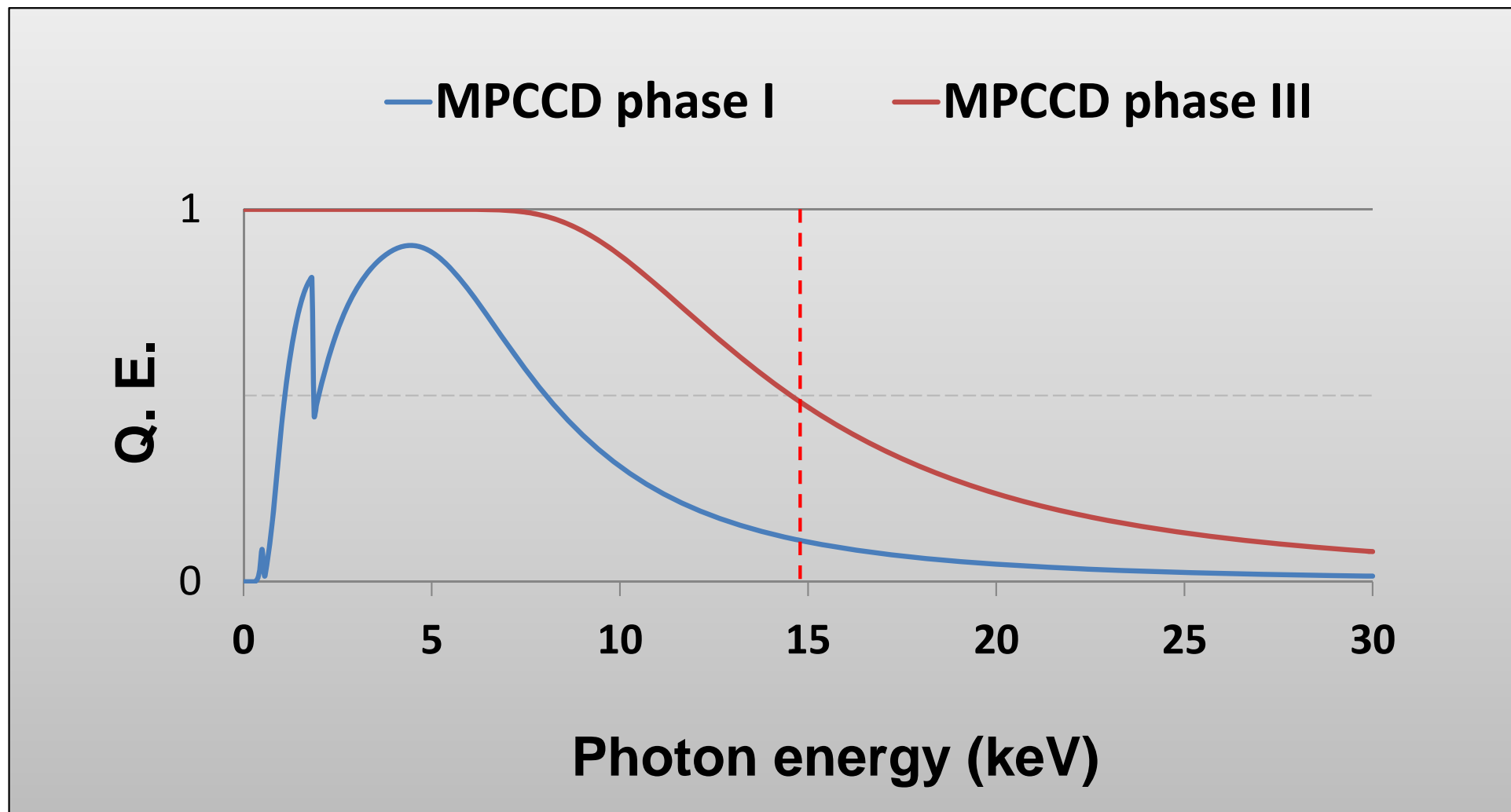
Description	Phase I*	Phase III**	Phase III-L**	Unit
Pixel Size	50 x 50			$\mu\text{m}^2$
Pixel Number	1024 (V) x 512 (H)			-
Readout Port	8			-
Wafer	Epitaxial	FZ		-
Illumination Side	Front	Back		-
Sensor Thickness	50	300	300	$\mu\text{m}$
Quantum Efficiency	78	99	99	% for 6 keV
	19	73	73	% for 12 keV
Conversion Gain	0.5	0.5	2.0	$\mu\text{V}/\text{e}^-$
Detection Noise	100-250	300	60	$\text{e}^- \text{ rms}$
Peak Signal	4.1-5	3.4	1.6	$\text{Me}/\text{pixel}$
	16.4-20	13.6	6.4	$\text{Me}/100\mu\text{m}^2$
Radiation Hardness	1.1	1	1	$\text{MGy}$ for 12 keV X-rays

\*: T. Kameshima et.al., Review of Scientific Instruments, 85, 033110 (2014).

\*\* : S. Ono et.al., in preparation.

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# Quantum Efficiency of MPCCD Phase III





# X-ray Transmission Image by MPCCD Phase III

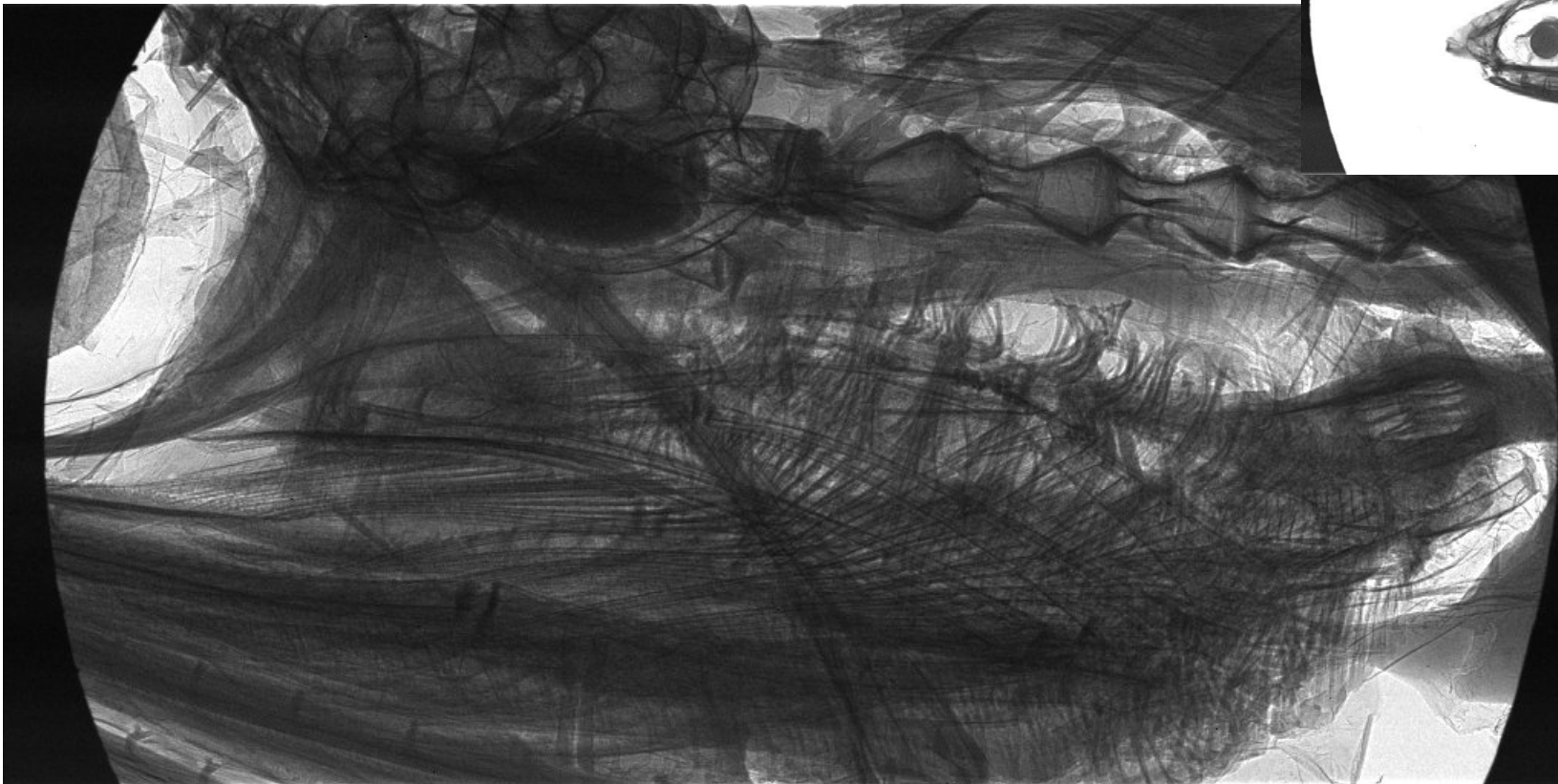
17

Source-sample : 380 mm  
Detector-sample : 890 mm  
X-ray (Cu target) : 40 kV, 100  $\mu$ A  
X-ray source size :  $\sim$ 65  $\mu$ m  
Exposure time : 100 msec  
Temperature :  $-20^{\circ}\text{C}$

Average of 100 frames

Gain calibration among output ports

Background and flat field correction



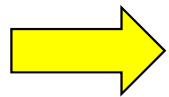
Dried fish

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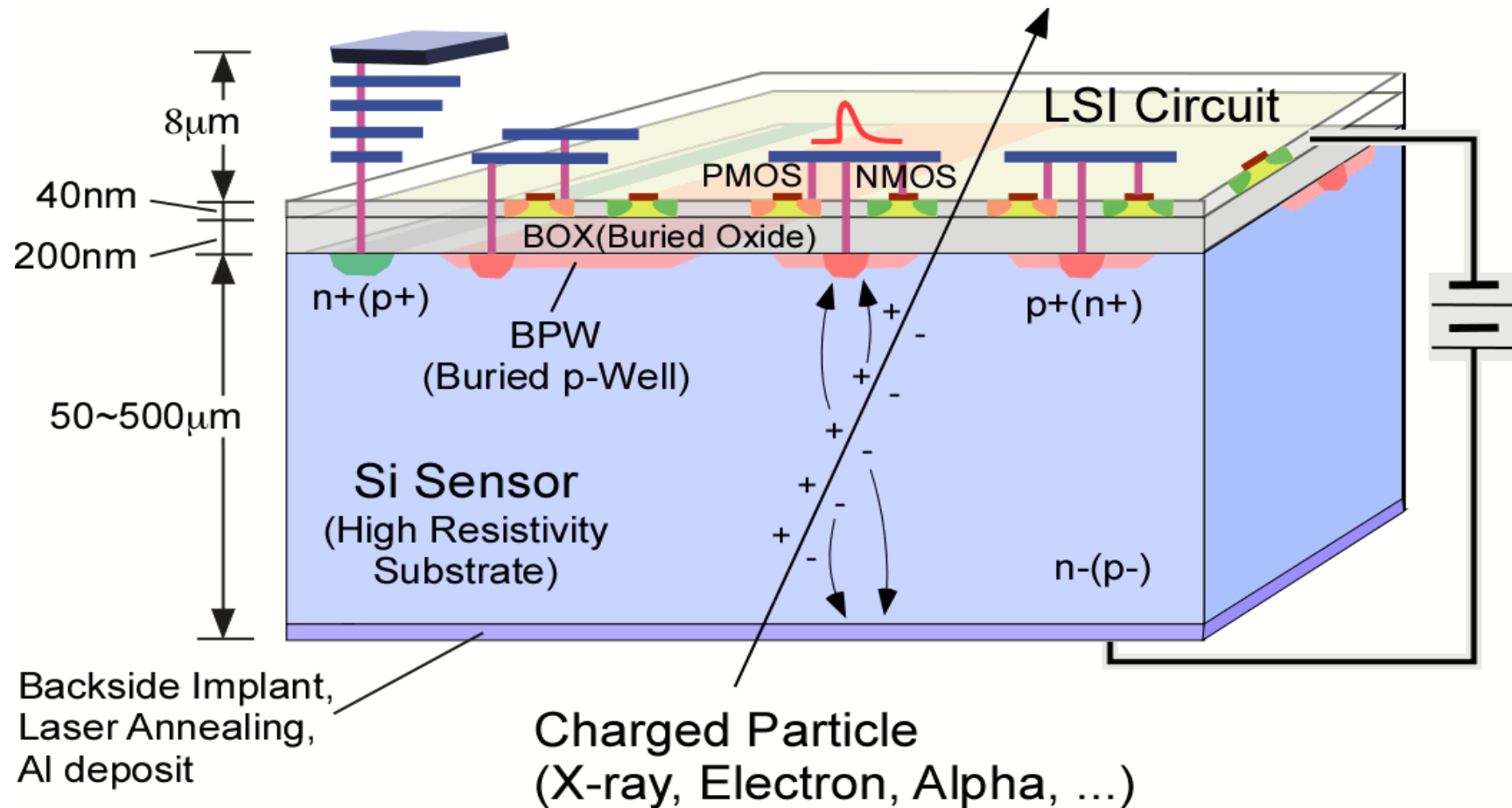


4. SOPHIAS (Silicon-On-Insulator Photon Imaging Array Sensor)

5. New Image Sensor Plan

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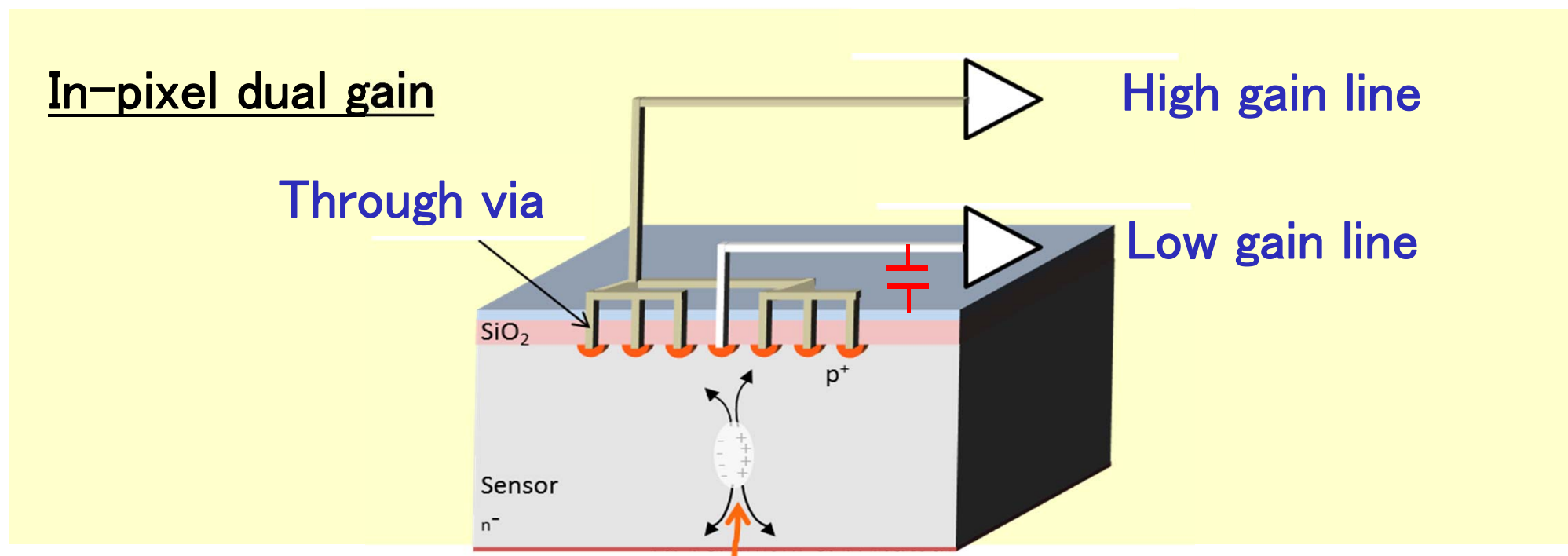
# SOI Pixel Detector Architecture (SOIPIX Collaboration)<sup>19</sup>



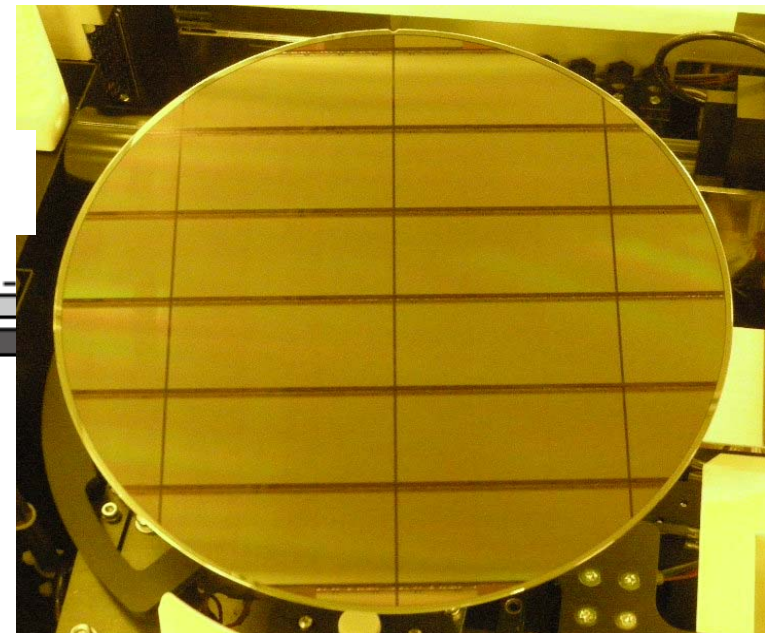
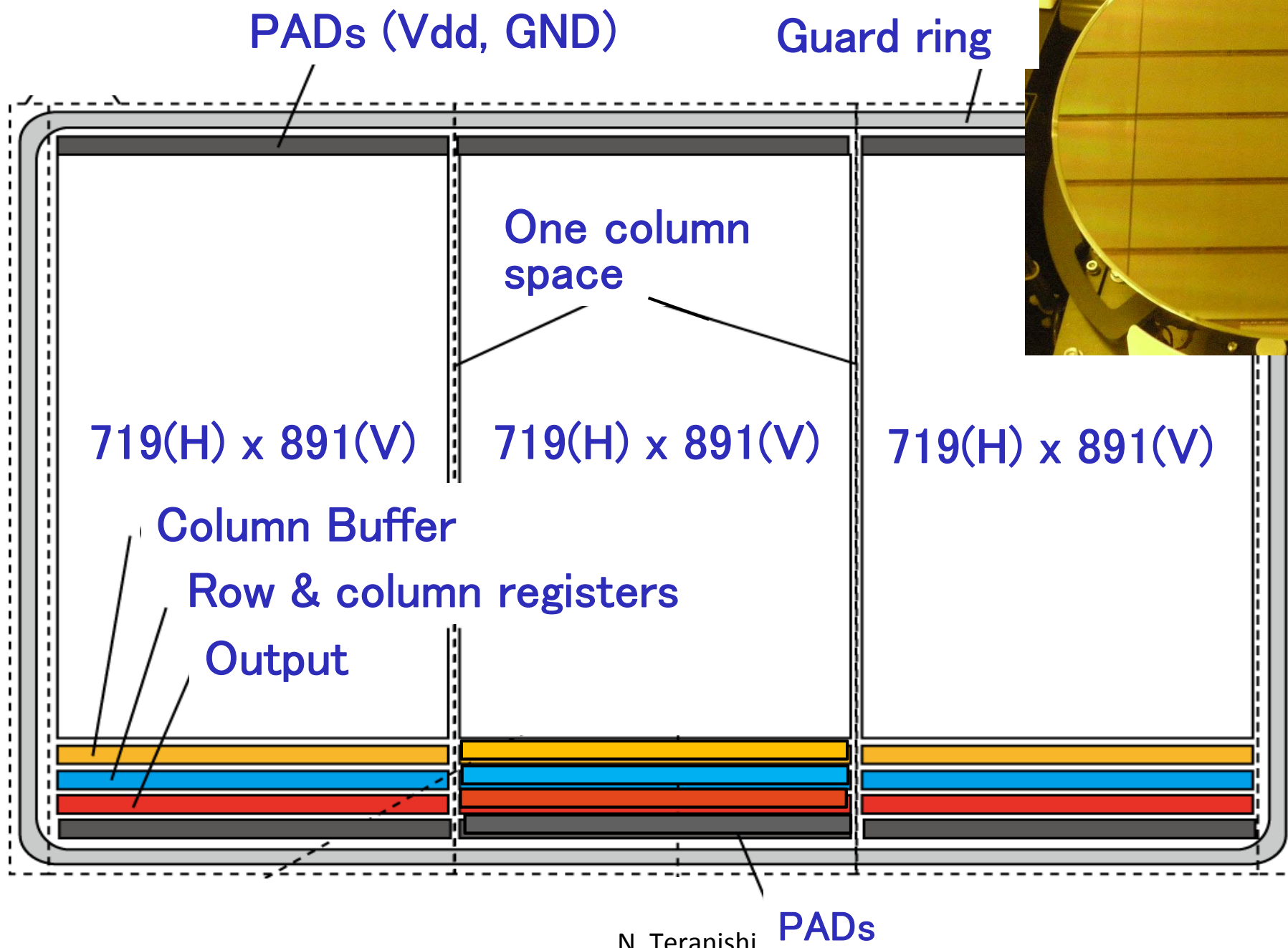
- High resistivity substrate for support → 500 um thick sensor
- Readout circuits and sensor are optimized independently
- Readout circuits can use almost all pixel area.
- Large saturation, 7 Me<sup>-</sup> by MIM and CMOS circuit

# SOPHIAS (Silicon-On-Insulator Photon Imaging Array Sensor)

Specifications	SOPHIAS	MPCCD Phase I
Pixel Size	30 $\mu\text{m}$	50 $\mu\text{m}$
Pixel Number	1.9 Mpixel	0.5 Mpixel
Frame Rate	60 fps	60 fps
Dual Gain Line	In-pixel	In-Camera
Random Noise	150 e-rms @ High gain	250 e-rms
Saturation Signal	7 Me-/pixel @ low gain	4.1-5 Me-/pixel

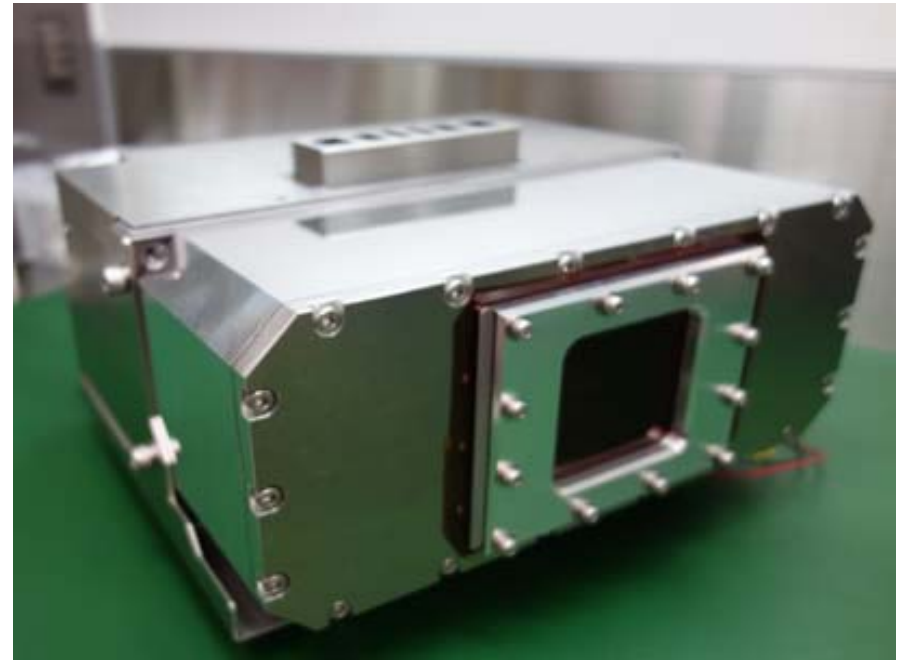


# Floor Plan



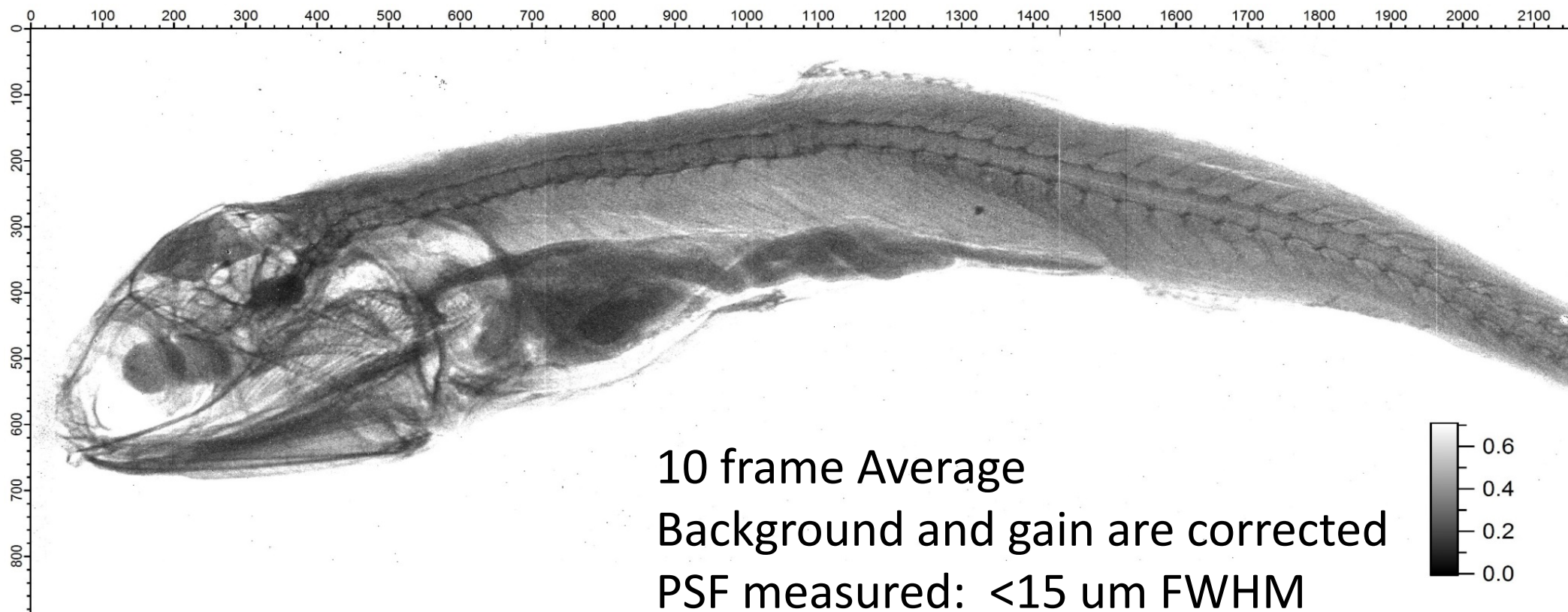
# Schedule of SOPHIAS

- **Now**
  - **Sensor evaluation & improvement**
- **Dual Sensor Detector**
  - **3.8 Mpixels**
- **Target:**
  - **Coherent X-ray Imaging**
- **Fall 2014**
  - **In-house test campaign**



Dual Sensor Detector

# X-ray Transmission Image

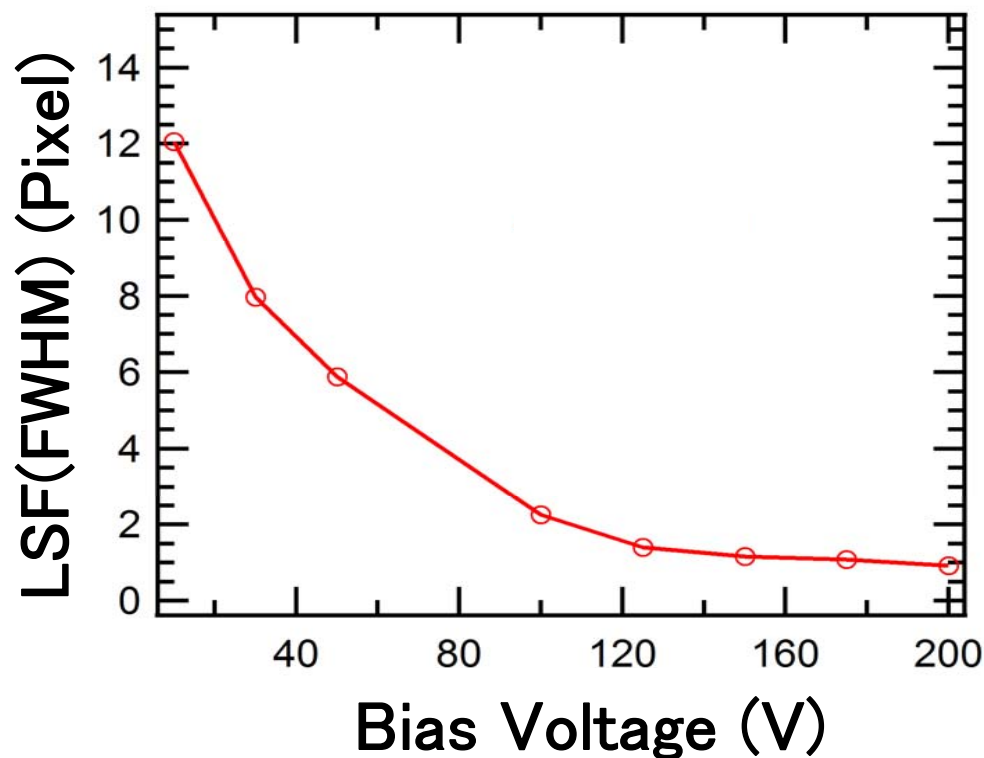


**Source-sample : 200 mm**  
**Detector-sample : 600 mm**  
**X-ray (Cu target) : 40 kV, 800  $\mu\text{A}$**   
**X-ray source size :  $\sim 3\text{ }\mu\text{m}$**   
**Exposure time : 10 msec**  
**Temperature : Room Temp.**



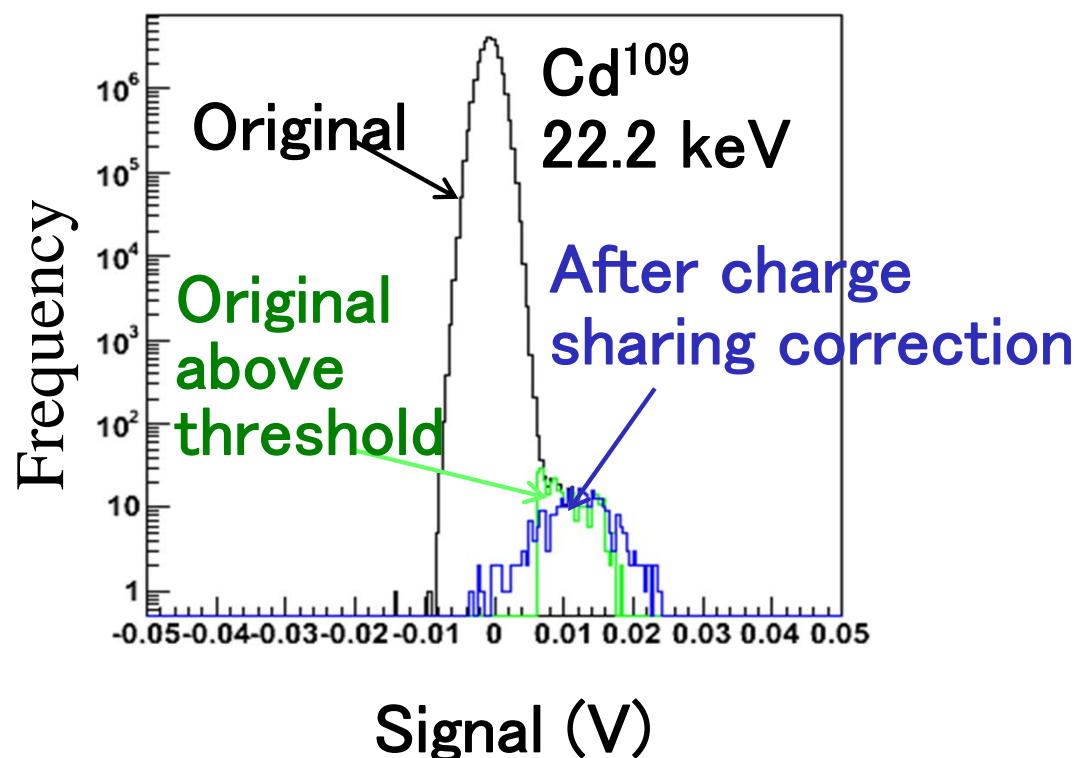
# Performance Evaluated

- $7 \text{ k}\Omega \text{ cm}$ ,  $500 \mu\text{m}$  substrate is fully depleted at more than  $120 \text{ V}$ .
- LSF(FWHM) :  $33 \mu\text{m}$  (1.1 pixel)
- Single photon is detected, but the existence of some signal loss is suggested.



Spatial Resolution

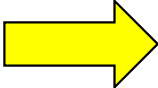
Cu Ka irradiation 40 kV 300  $\mu\text{A}$



Single Photon Detection



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# SPring-8 will Power up to be SPring-8 II

## New Feature

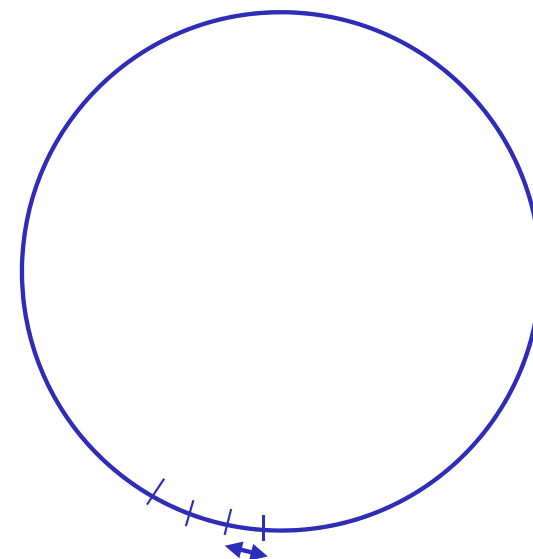
- X-ray focus size at full irradiation : 1 $\mu$ m  $\rightarrow$  10nm in diameter
- Coherent flux : 0.1%  $\rightarrow$  10–20%

## Ring Parameters

Item	Time	Frequency
Pulse width	$\sim$ 50ps	
Pulse interval (bucket interval)	2ns (1.965ns)	508.810MHz
Revolution (2,436 buckets)	4.786 $\mu$ s	208.87kHz

## Proposed schedule

- Q1 2019 : SPring-8 blackout
- Q2 2020 : Beam line commissioning
- Q1 2021 : First science



- 2ns interval
- 2,436 buckets on ring

# New Image Sensor for SPring-8 II (Tentative)

- Mode A. High frame rate mode: 52.2 kfps  
To synchronize with 1/4 full revolution frequency of 208.87 kHz
- Mode B. High speed burst mode: 10 ns interval  
To observe mesoscopic dynamics at atomic scale.
- Mode C. Large full count rate mode ( $\equiv$  (Saturation) x (Frame rate))  
To reduce statistical error and to shorten measuring time.

	Electron	Photon@12.4 keV
Saturation	6.25 Me <sup>-</sup>	1840 photon
Full count rate	130 Ge <sup>-</sup> /s	38 Mphoton/s

Frame rate: 20.88kfps

# Data Rate (Mode A)

## Assumptions:

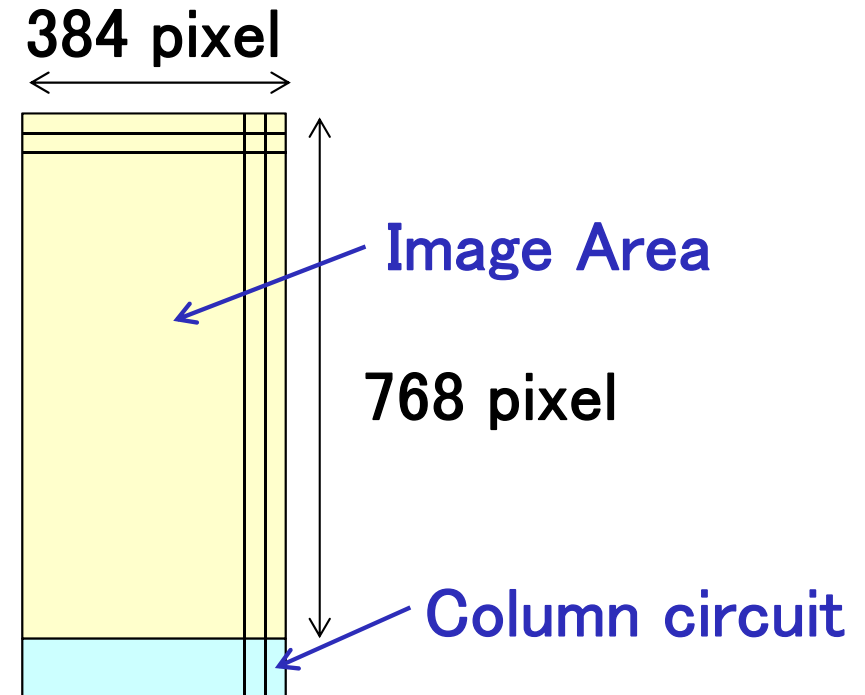
1. Pixel number: 384 (H) x 768 (V)
2. Frame rate: 52.2 kfps  
Frame period: 19.2 ns  
Then, horizontal period (1H):  
 $19.2 \text{ ns} / 768 = 24.9 \text{ ns}$  (40 MHz)
3. ADC resolution: 12 bit

Date rate from 1 column:

$$40 \text{ MHz} \times 12 \text{ bit} = 480 \text{ Mbps}$$

Date rate from 1 chip:

$$480 \text{ Mbps} \times 384 = 185 \text{ Gbps}$$



- Date rates for Mode B & C are set as same as Mode A.

# Comparison with SHV (Super Hi-Vision)

- Data rate is 3.6 times larger than SHV.

➔ Digital output is suitable.

	SHV (8k) *	New sensor Mode A	Ratio
Pixel area	2.8 $\mu\text{m}$ $\square$	70 $\mu\text{m}$ $\square$	625
Total pixel number	7808(H) x 4336(V)	384(H) x 768(V)	0.0087
Frame rate	120 fps	52.2 kfps	435
Saturation	7 $\text{ke}^-$ (Estimated)	140 $\text{ke}^-$	20
ADC resolution	12 bit	12 bit	1
Random noise	3.0 $\text{e}^-$ @gain=7.5	60 $\text{e}^-$	20
Data rate	51 Gbps	185 Gbps	3.6
Power consumption	2.67 W @gain=7.5	5 W	1.87
Year	2012	2017	–

\*: Kitamura et al. (NHK, Shizuoka U., Brookman Tech.), IEEE Trans. ED, vol. 59, p. 3425 (2012).

# Analog Output vs Digital Output

- Digital output looks better, which is main stream in industry.
- 2 or 3 times faster ADC is still needed.

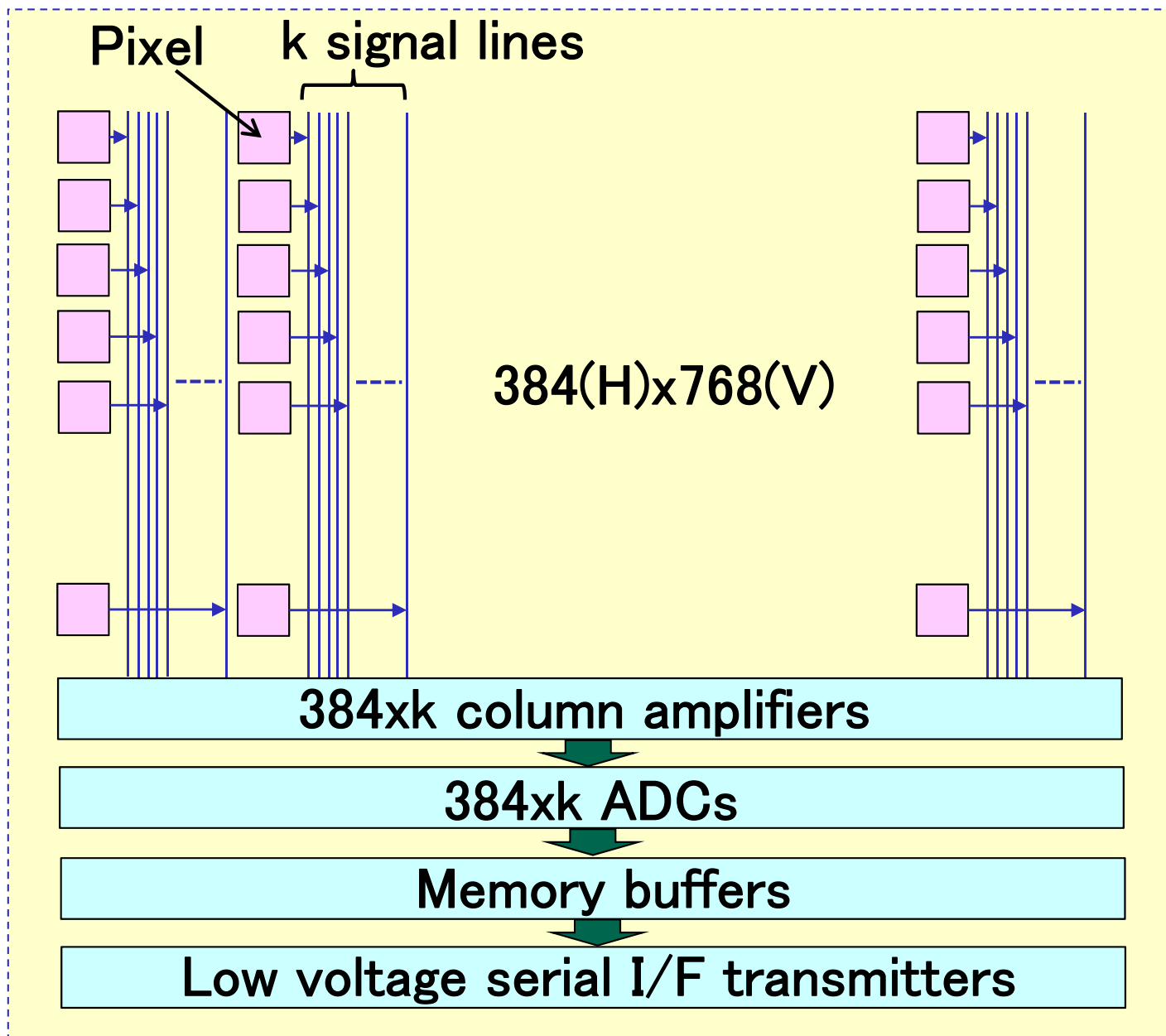
	Analog	Digital
Data Rate/Port	20 MHz x 12 bit equiv.	<b>2.3 Gbps (sub-LVDS)**</b>
# of Port/Column	2 Port/Column	<b>1/4 Port/Column</b>
Power (ADC)	None	<b>101 uW * x 70 x 384 = 2.7 W (70 ADC/Column)</b>
(IO)	<b>6 mW x 2 x 384 = 4.6 W</b>	<b>12.5 mW** x 1/4 x 384 = 1.2 W</b>
(ADC + IO)	<b>4.6 W</b>	<b>3.9 W</b>
Chip Size (Circuit)	<b>Smaller</b>	Larger
(PAD)	Larger	<b>Smaller</b>
Crosstalk	<b>Worse</b>	<b>Better</b>

\*: Kitamura et al. (NHK, Shizuoka U., Brookman Tech.), IEEE Trans. ED, vol. 59, p. 3425 (2012).

\*\* : T. Toyama et al. (Sony), IEEE ISSCC, 23.11, p.420 (2011).

# Configuration of New Sensor for SPring-8 II

- k vertical signal lines.
  - Settling time
  - ADC time
- Column parallel.
- On-chip ADC.
- High speed serial digital out.
- 3 side butttable.



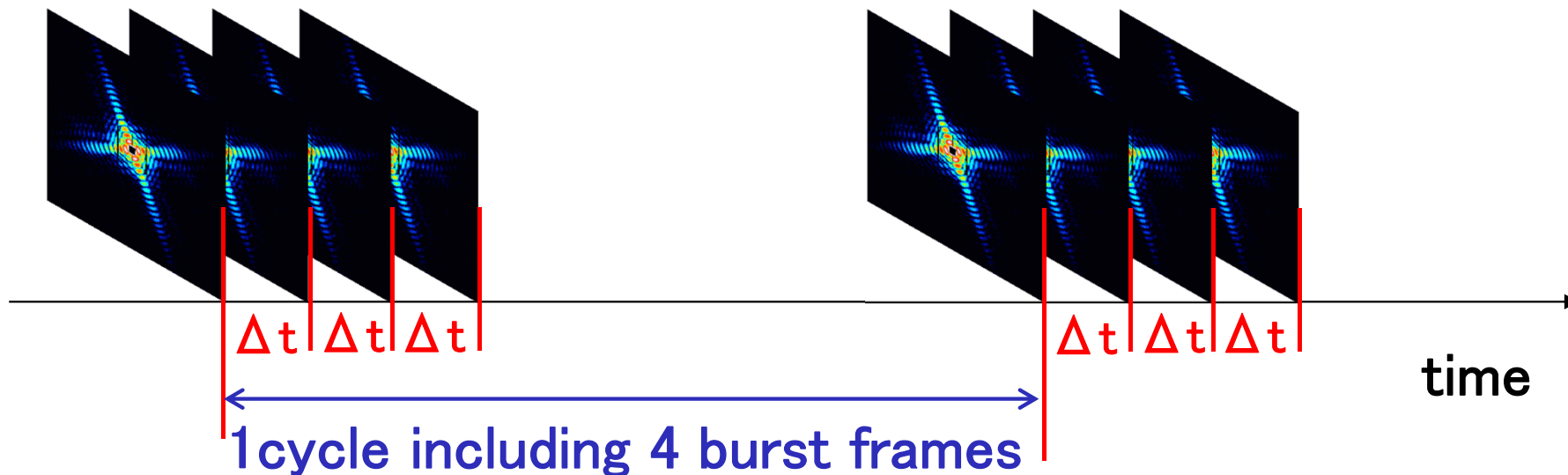
# High Speed Burst Mode (Mode B)

## Motivation:

- To observe mesoscopic dynamics at atomic scale.
- Diffraction correlation gives information on the atomic motion.

## Target:

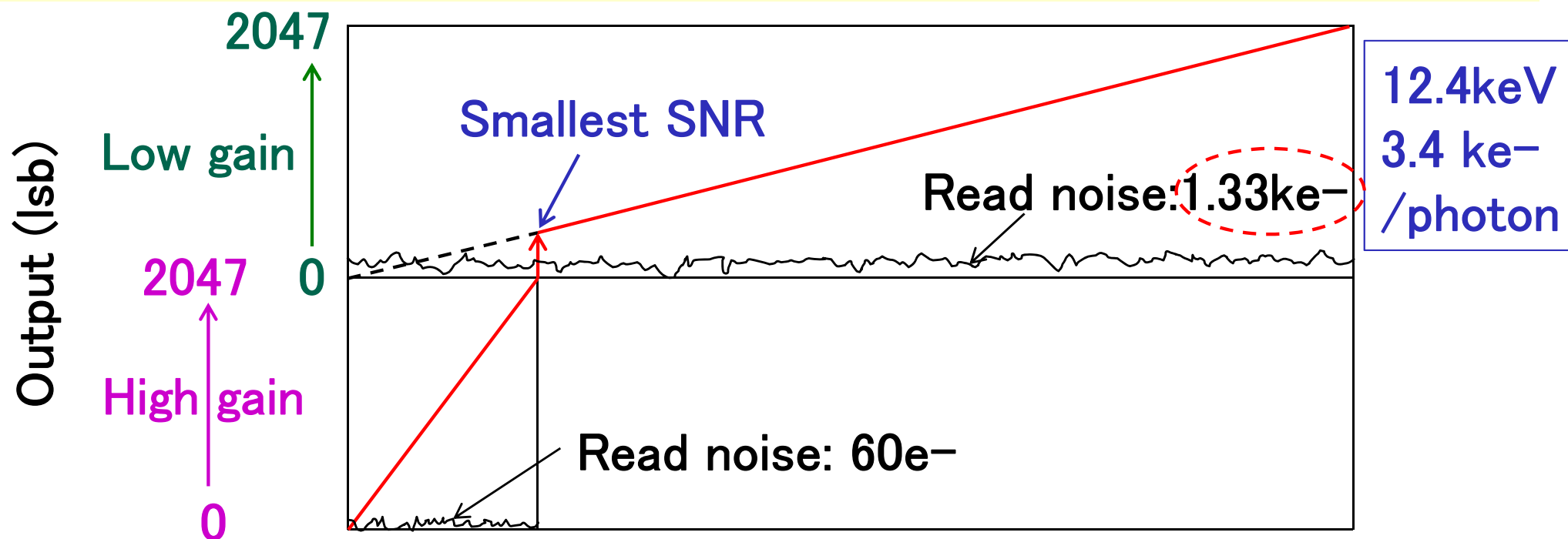
- 10 ns burst mode ( $\Delta t = 10$  ns)
- # of burst frames: 2, or 4, or 8
- 1 cycle = 52.2 kfps / # of burst frames





# Large Full Count Rate Mode (Mode C)

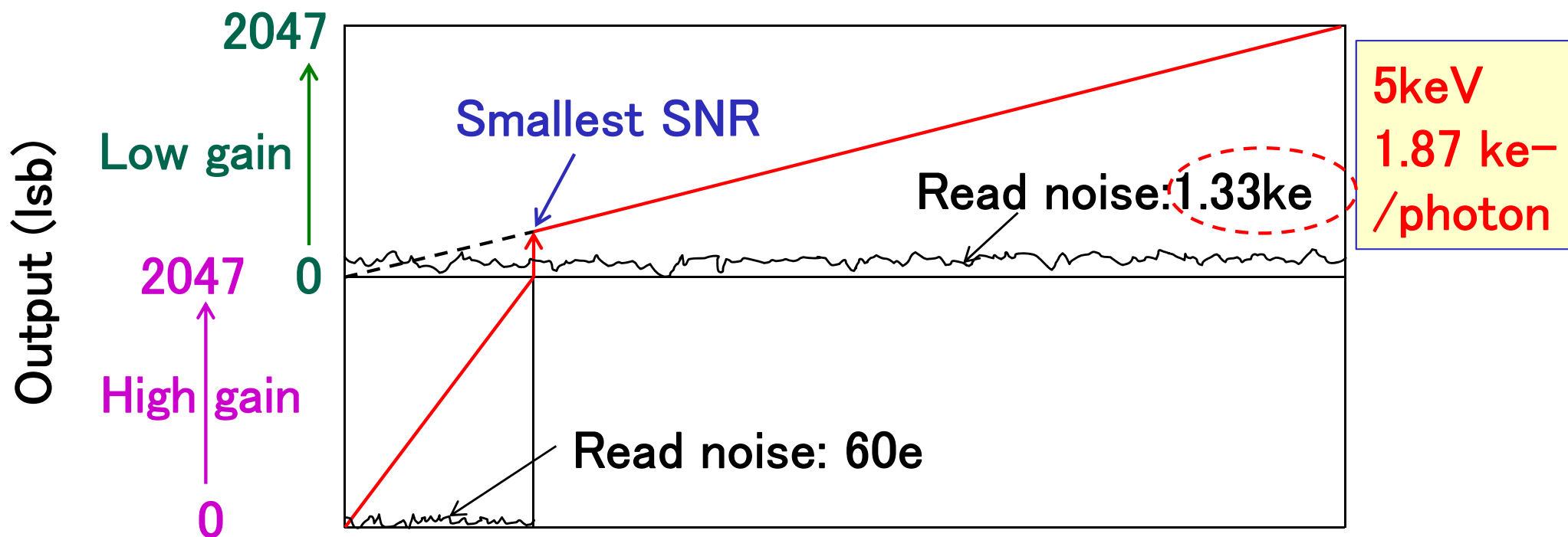
- Each pixel has 2 different detection capacitance, which realize **high gain pass** and **low gain pass**.
- Read noise is at most 9% (12.4 keV) of photon shot noise.



Signal	0 e <sup>-</sup> 0 photon	72 ke <sup>-</sup> 21.2 photon	6,250 ke <sup>-</sup> 1,840 photon
Photon shot noise		15.6 ke <sup>-</sup> 4.6 photon	146 ke <sup>-</sup> 43 photon

# Large Full Count Rate Mode (Mode C)

- If incident X-ray energy is decreased, photon shot noise at electron is decreased.
- Read noise is at crossover point is 11% (5keV) of photon shot noise.



Signal	0 e <sup>-</sup> 0 photon	72 ke <sup>-</sup> 38.5 photon	6,250 ke <sup>-</sup> 3,340 photon
Photon shot noise		11.6 ke <sup>-</sup> 6.2 photon	108 ke <sup>-</sup> 58 photon

# Combination of Modes

## Target:


- Mode A and Mode B will be realized on one image sensor.
- Preferably, all three modes will be realized on one image sensor.

**Mode A**  
High frame rate mode

**Mode B**  
High speed burst mode

**Mode C**  
Large full count rate mode

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# Summary

## 1. MPCCD

- Phase I sensor is used for 70–80 % applications at SACLA.
- Phase III sensor with 300  $\mu\text{m}$  depletion depth and Phase III–L with 60  $e^-$  rms noise are under development.

## 2. SOPHIAS is under development

- SOI Pixel Detector (SOIPIX Collaboration)
- Saturation: 7  $\text{Me}^-$  at 30  $\mu\text{m}$  pixel
- High gain pass & low gain pass are implemented.

## 3. New sensor for SPring-8 II and SACLA is under planning.

- High frame rate mode: 52.2 kfps
- High speed burst mode: 10 ns interval
- Large full count rate mode  
≡ (Saturation) x (Frame rate): 130  $\text{GeV}/\text{s}$